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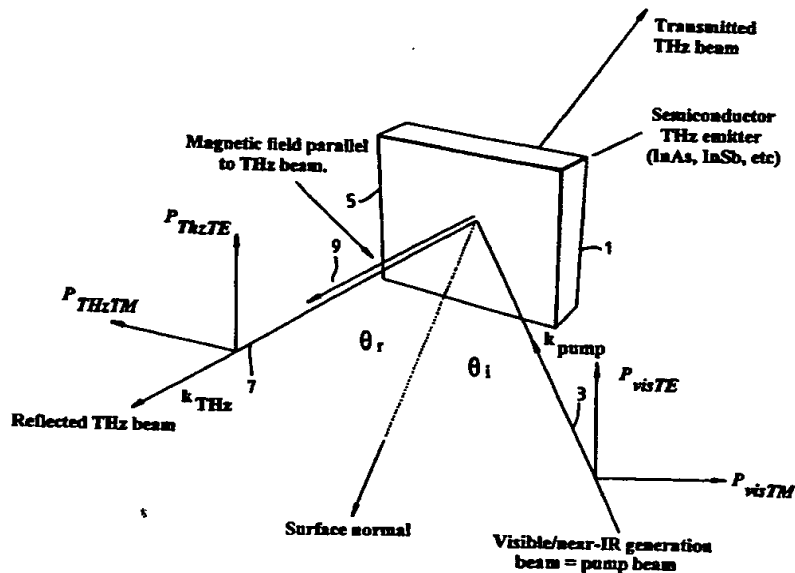
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9922859.5 27 September 1999 (27.09.1999) GB(71) Applicant (for all designated States except US):
TOSHIBA RESEARCH EUROPE LIMITED [GB/GB];
260 Cambridge Science Park, Milton Road, Cambridge,
Cambridgeshire CB4 0WE (GB).

(72) Inventors; and

(75) Inventors/Applicants (for US only): ARNONE, Donald,
Dominic [US/GB]; c/o Toshiba Research Europe Limited,Cambridge Research Laboratory, 260 Cambridge Science
Park, Milton Road, Cambridge CB4 0WE (GB). CIESLA,
Craig, Michael [GB/GB]; c/o Toshiba Research Europe
Limited, Cambridge Research Laboratory, 260 Cambridge
Science Park, Milton Road, Cambridge CB4 0WE (GB).(74) Agent: GRANLEESE, Rhian, Jane; Marks & Clerk,
57-60 Lincoln's Inn Fields, London WC2A 3LS (GB).(81) Designated States (national): AE, AG, AL, AM, AT, AU,
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(54) Title: A RADIATION SOURCE



(57) Abstract: A radiation source comprising a frequency conversion member (1) configured to emit a beam of emitted radiation (7) with at least one frequency in the range from 0.1 THz to 100 THz, in response to irradiation with an input beam (3) with a frequency different to that of the emitted radiation (7), the source being subjected to a magnetic field (9) which has a component parallel to that of the emitted beam of radiation (7). The radiation source may be optimised by using both the fluence of the input beam and the magnetic field or may comprise a magnetically doped frequency conversion member or also have means for applying an electric field.